

# Jaikwang Shin

## List of Publications by Year in descending order

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Version: 2024-02-01

18  
papers

875  
citations

759233

12  
h-index

940533

16  
g-index

18  
all docs

18  
docs citations

18  
times ranked

1296  
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrically driven mid-submicrometre pixelation of InGaN micro-light-emitting diode displays for augmented-reality glasses. <i>Nature Photonics</i> , 2021, 15, 449-455.	31.4	91
2	Deep-learning-based inverse design model for intelligent discovery of organic molecules. <i>Npj Computational Materials</i> , 2018, 4, .	8.7	91
3	Computational approaches for investigating interfacial adhesion phenomena of polyimide on silica glass. <i>Scientific Reports</i> , 2017, 7, 10475.	3.3	27
4	Overview of the Oxygen Behavior in the Degradation of $\text{Li}_2\text{MnO}_3$ Cathode Material. <i>Journal of Physical Chemistry C</i> , 2017, 121, 21118-21127.	3.1	30
5	Understanding the grain-growth mechanism of high-performance organic semiconducting diphenyl-dibenzothiopheno[6,5-b:6 $\epsilon$ :5 $\epsilon$ -f]thieno[3,2-b]thiophene molecules. <i>Applied Physics Letters</i> , 2017, 111, 233301.	3.3	2
6	The prediction of hole mobility in organic semiconductors and its calibration based on the grain-boundary effect. <i>Physical Chemistry Chemical Physics</i> , 2016, 18, 21371-21380.	2.8	9
7	A comparative study of structural changes in lithium nickel cobalt manganese oxide as a function of Ni content during delithiation process. <i>Journal of Power Sources</i> , 2016, 315, 111-119.	7.8	122
8	Interfacial adhesion behavior of polyimides on silica glass: A molecular dynamics study. <i>Polymer</i> , 2016, 98, 1-10.	3.8	59
9	p-GaN Gate HEMTs With Tungsten Gate Metal for High Threshold Voltage and Low Gate Current. <i>IEEE Electron Device Letters</i> , 2013, 34, 202-204.	3.9	213
10	Source-Connected p-GaN Gate HEMTs for Increased Threshold Voltage. <i>IEEE Electron Device Letters</i> , 2013, 34, 605-607.	3.9	35
11	Analysis of DC/transient current and RTN behaviors related to traps in p-GaN gate HEMT. , 2013, , .		7
12	The impact of active layer thickness on low-frequency noise characteristics in InZnO thin-film transistors with high mobility. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	38
13	Characterization of traps and trap-related effects in recessed-gate normally-off AlGaN/GaN-based MOSHEMT. , 2012, , .		18
14	Surface Ferromagnetic p-Type ZnO Nanowires through Charge Transfer Doping. <i>ACS Applied Materials &amp; Interfaces</i> , 2012, 4, 1365-1370.	8.0	5
15	Verification of Interface State Properties of a-InGaZnO Thin-Film Transistors With $\text{SiN}_x$ and $\text{SiO}_2$ Gate Dielectrics by Low-Frequency Noise Measurements. <i>IEEE Electron Device Letters</i> , 2011, 32, 1083-1085.	3.9	48
16	Influence of Hf contents on interface state properties in <i>a</i> -HfInZnO thin-film transistors with $\text{SiN}_x/\text{SiO}_x$ gate dielectrics. <i>Applied Physics Letters</i> , 2011, 99, .	3.3	32
17	Impacts of fluorine on GaN high electron mobility transistors: Theoretical study. <i>Physica Status Solidi - Rapid Research Letters</i> , 2010, 4, 332-334.	2.4	10
18	Asymmetric Doping in Silicon Nanostructures: The Impact of Surface Dangling Bonds. <i>Nano Letters</i> , 2010, 10, 1671-1676.	9.1	38